

BRCS900P10DP

Rev.A Aug.-2023

/ Descriptions

TO-252 P MOS
P-CHANNEL MOSFET in a TO-252 Plastic Package.

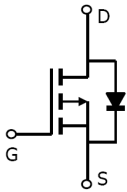
/ Features

$V_{DS}(V)=-100V$ $I_D=-18A$
 $R_{DS(ON)}@-10V<90m$ (Typ.80mR)
 $R_{DS(ON)}@-4.5V<100m$ (Typ.90mR)
HF Product.

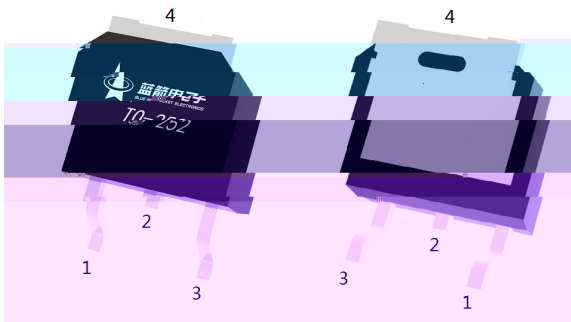
/ Applications

DC/DC
Power Management of Industrial DC/DC Converter.

/ Equivalent Circuit



/ Pinning



PIN1 G PIN 2 D PIN 3 S PIN 4 D

/ Marking

See Marking Instructions.

/ Absolute Maximum Ratings($T_a=25$)

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	-100	V
Drain Current - Continuous		$I_D(T_c=25)$	-18	A
Drain Current – Pulsed		I_{DM}	-54	A
Gate-Source Voltage		V_{GS}	± 20	V
Power Dissipation		$P_D(T_c=25)$	65	W
Single Pulse Avalanche Energy(L=0.5mH)		E_{AS}	185	mJ
Avalanche Current(L=0.5mH)		I_{AS}	-21.5	A
Junction and Storage Temperature Range		T_j, T_{stg}	-55 to 150	
Thermal resistance, junction - ambient	Steady-State	R_{JA}	63	/ W
Thermal resistance, junction - case	Steady-State	R_{JC}	1.92	

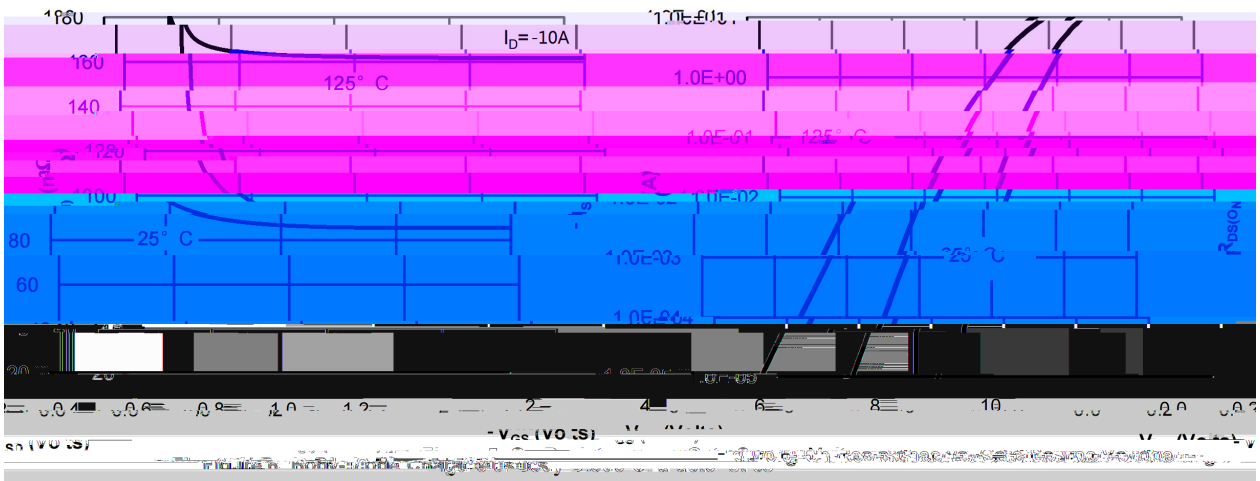
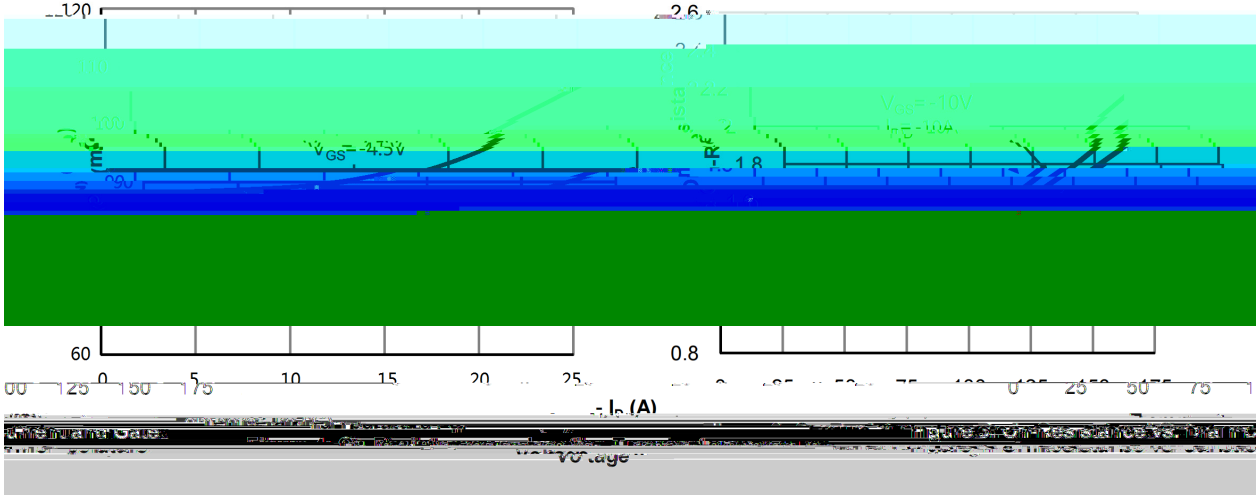
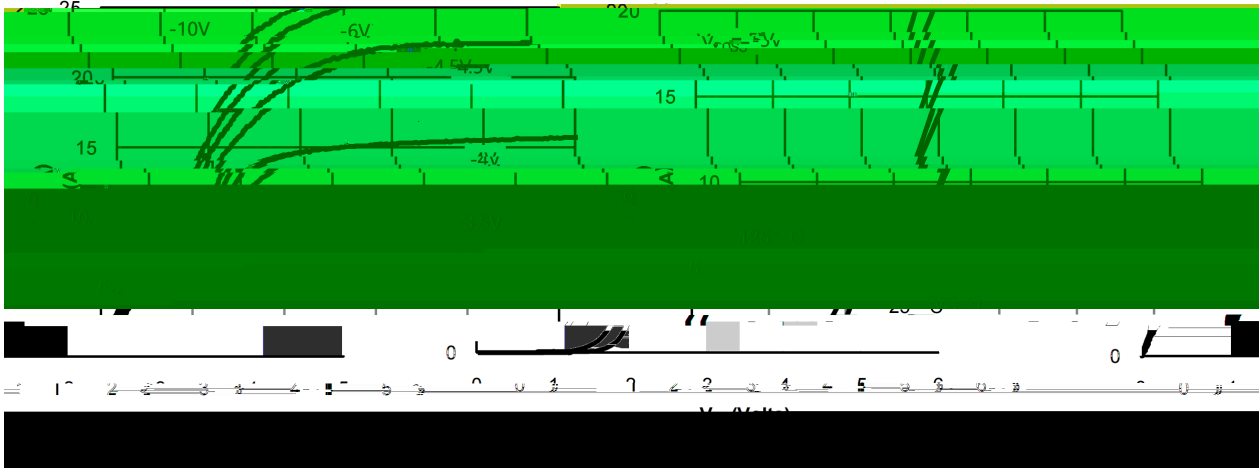
/ Electrical Characteristics($T_a=25$)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=-250\mu A$ $V_{GS}=0V$	-100	-110		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-100V$ $V_{GS}=0V$			-1	μA
Gate-Body leakage current	I_{GSS}	$V_{DS}=0V,$ $V_{GS}=\pm 20V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=-250\mu A$	-1	-1.7	-2.5	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=-10V,$ $I_D=-10A$		80	90	m
		$V_{GS}=-4.5V,$ $I_D=-10A$		90	100	
Diode Forward Voltage	V_{SD}	$I_S=-1A,$ $V_{GS}=0V$			-1.2	V
Input Capacitance	C_{iss}	$V_{DS}=-15V$ $V_{GS}=0V$ $f=1.0MHz$		5200		pF
Output Capacitance	C_{oss}			750		
Reverse Transfer Capacitance	C_{rss}			450		
Gate resistance	R_g	$V_{GS}=0V$ $V_{DS}=0V$ $f=1MHz$		4.2		
Total Gate Charge	$Q_{g(10V)}$	$V_{GS}=-10V,$ $V_{DS}=-50V,$ $I_D=-5A$		5.9		nC
Total Gate Charge	$Q_{g(4.5V)}$			2.7		
Gate Source Charge	Q_{gs}			1.2		
Gate Drain Charge	Q_{gd}			1.2		

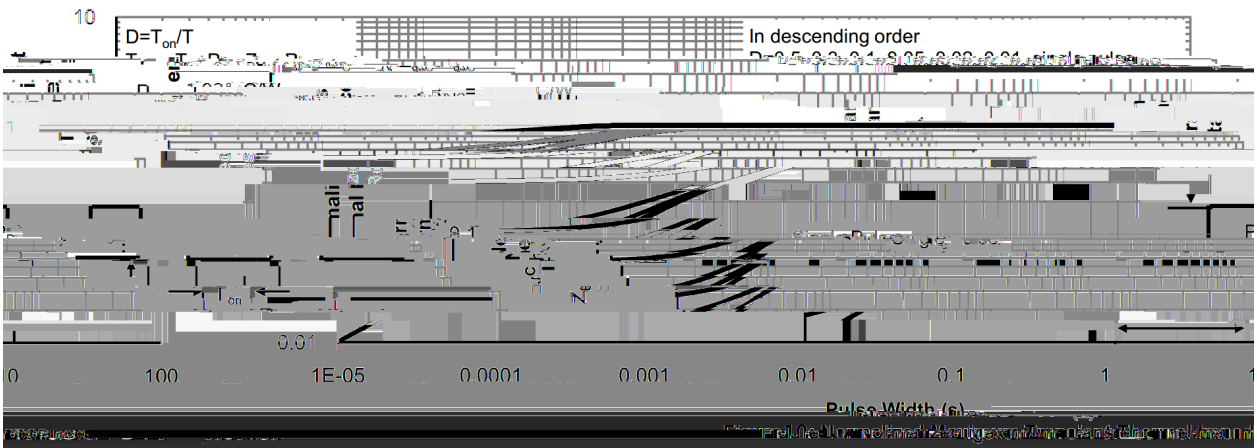
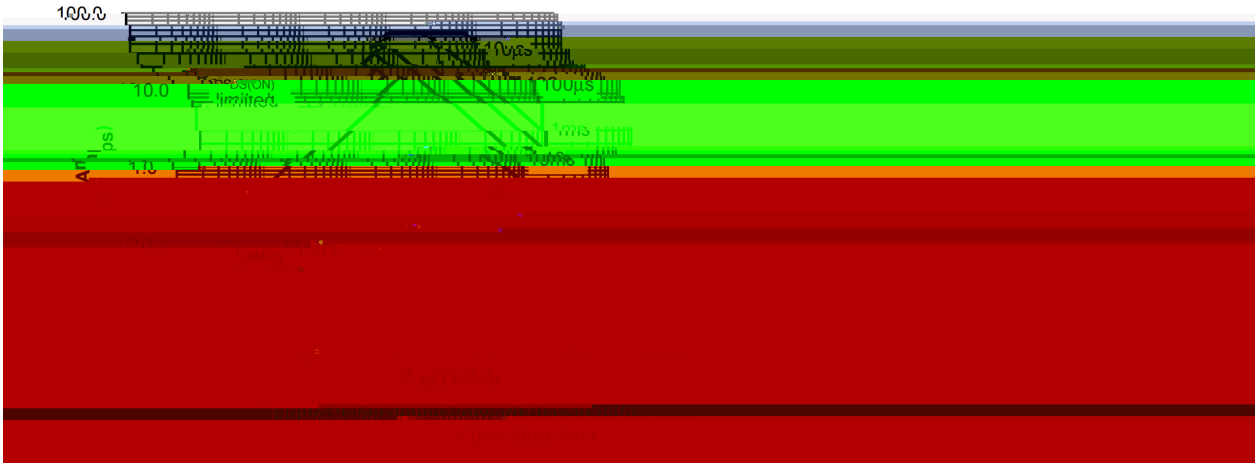
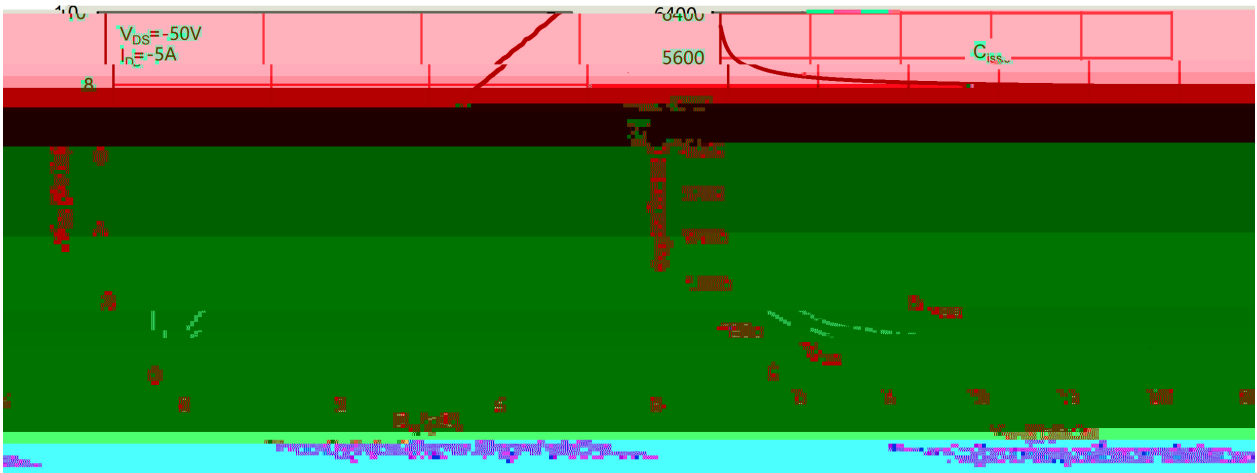
Parameter

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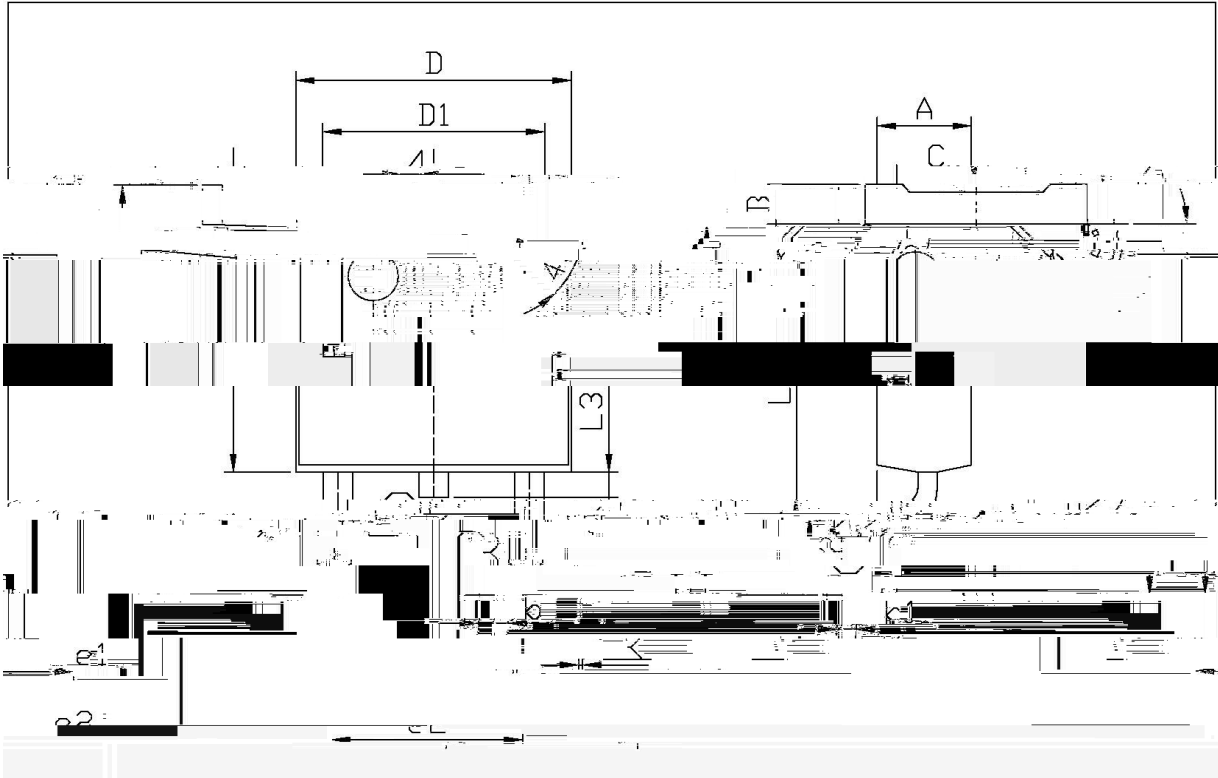
/ Electrical Characteristic Curve



/ Electrical Characteristic Curve



/ Package Dimensions

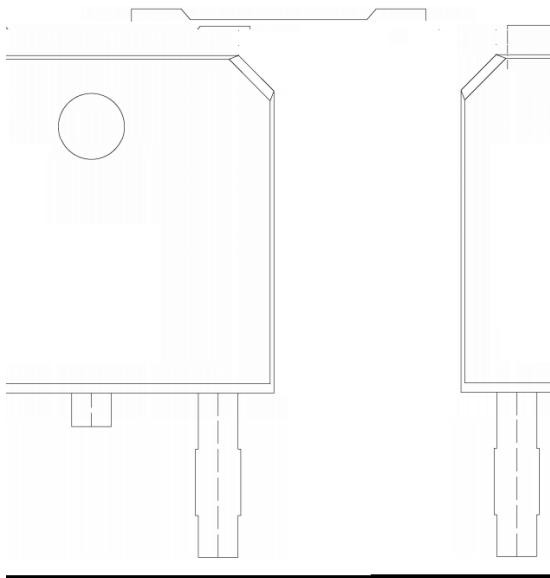


单位: mm

Dimensions, Millimeters		Dimensions, In Millimeters	
Min.	Max.	Min.	Max.
5.23	5.23	0.20	0.20
2.34	2.34	0.95	1.25
0.73	0.73	0.30	0.60
10.35	10.35	0.45	0.55
0.00	0.00	0.55	0.55
0.00	0.00	6.45	6.75
0.00	0.00	5.10	5.50
0.00	0.00	0.60	0.60

TO-252

/ Marking Instructions



BR
900P10

() / Temperature Profile for IR Reflow Soldering(Pb-Free)